ECE 65: Components & Circuits Lab

Lecture 22

Common collector amplifier parameters

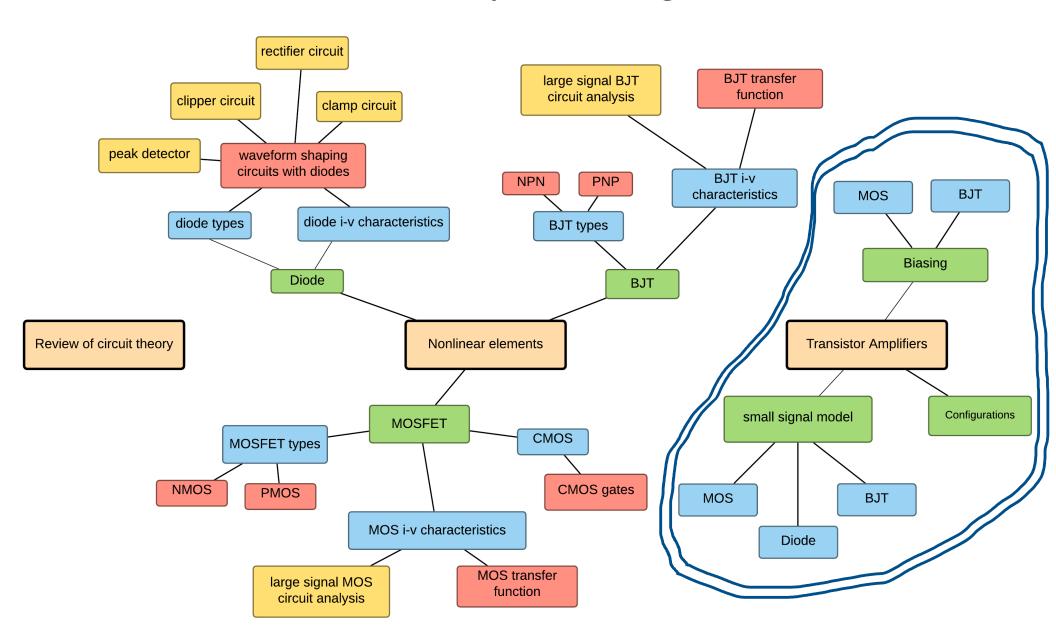
Reference notes: sections 6.1, 6.2

Sedra & Smith (7th Ed): sections 7.3

Saharnaz Baghdadchi

Course map

6. Transistor Amplifier Configurations

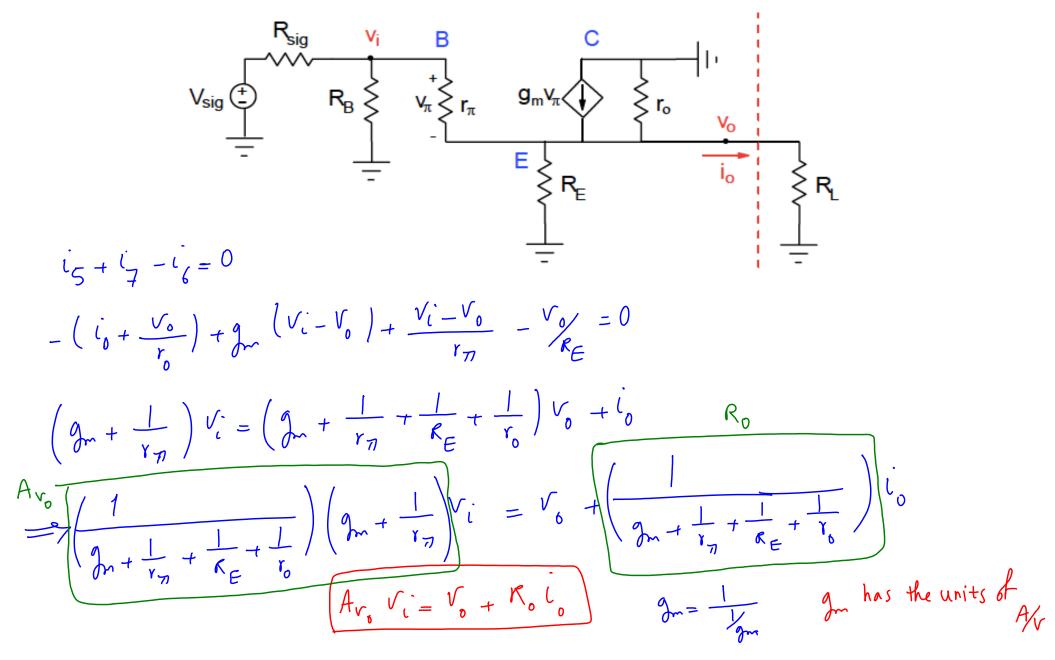


Derivation of A_{vo}, R_o, R_i for the common collector BJT amplifier

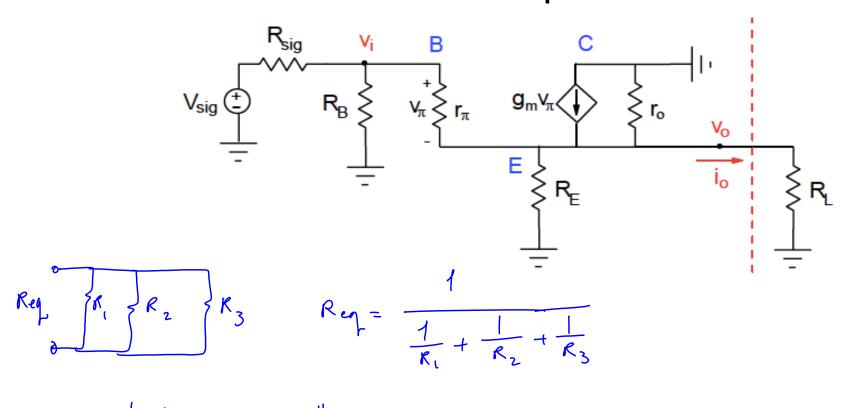
$$V_{\text{sig}} \stackrel{\downarrow}{=} V_{\text{sig}} V_{\text{i}} \stackrel{\downarrow}{=} V_{\text{i}}$$

Derivation of A_{vo}, R_o, R_i for the common collector

BJT amplifier



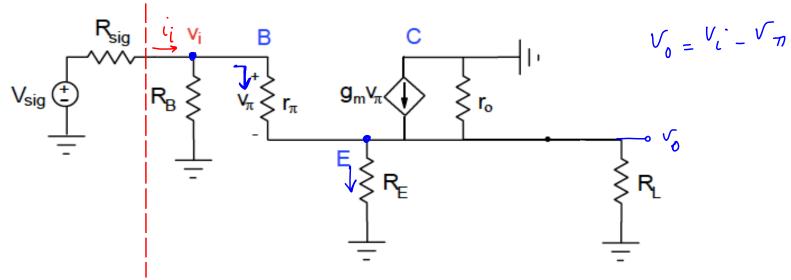
Derivation of A_{vo}, R_o, R_i for the common collector BJT amplifier



$$R_{o} = \left(\frac{1}{g_{m}}\right) \| r_{n} \| R_{E} \| r_{o}$$

$$A_{r_{o}} = \frac{\left(\frac{1}{g_{m}}\right) \| r_{n} \| R_{E} \| r_{o}}{\left(\frac{1}{g_{m}}\right) \| r_{n}}$$

Derivation of A_{vo}, R_o, R_i for the common collector BJT amplifier



$$R_{i} = \frac{V_{i}}{V_{i}}$$

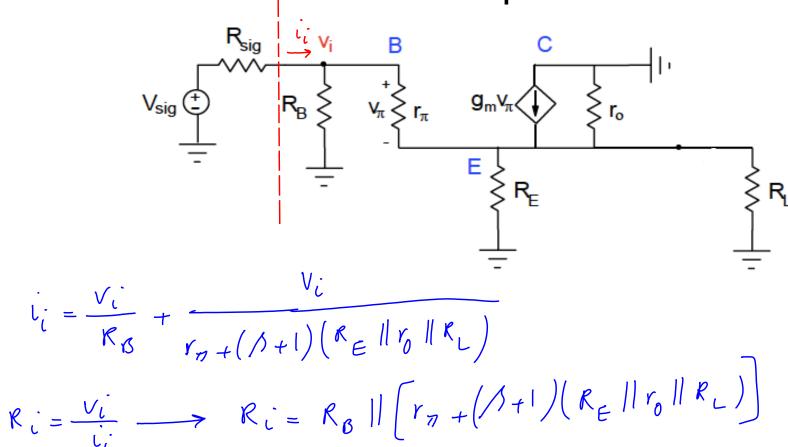
$$l_{i} = \frac{V_{i}}{R_{S}} + \frac{V_{D}}{Y_{D}}$$

$$\frac{\nabla_{n}}{r_{n}} + 2 \nabla_{n} = \left(\frac{\nabla_{i} - \nabla_{n}}{R_{E}}\right) + \left(\frac{\nabla_{i} - \nabla_{n}}{r_{o}}\right) + \frac{\nabla_{i} - \nabla_{n}}{R_{L}}$$

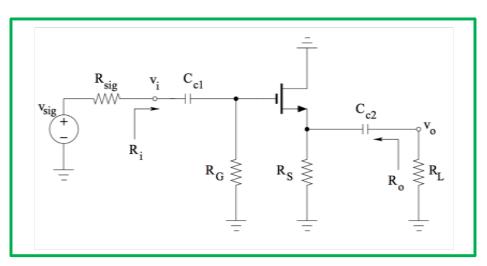
$$2 = \frac{3}{r_{n}} \qquad \rightarrow (3+1) \frac{\nabla_{n}}{r_{n}} = \frac{\nabla_{i} - \nabla_{n}}{R_{L}}$$

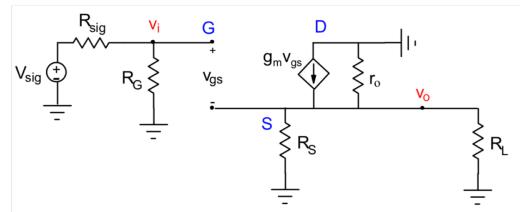
Derivation of Avo, Ro, Ri for the common collector

BJT amplifier

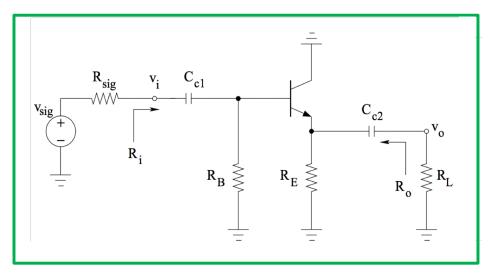


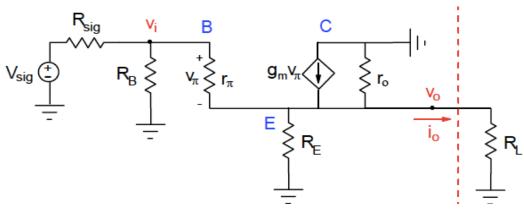
Common-Darin MOS amplifier parameters





Compare it with the signal circuit for a common collector BJT amplifier:





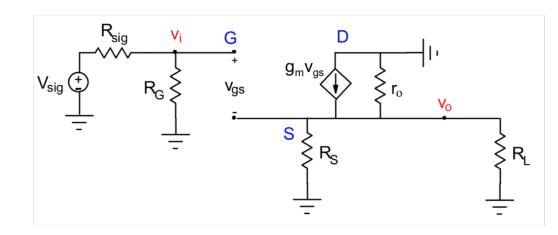
Common-Darin MOS amplifier parameters

In the derived equations for the common-collector BJT amplifier, replace R_B with R_G , R_E with R_S , and $r_\pi \to \infty$.

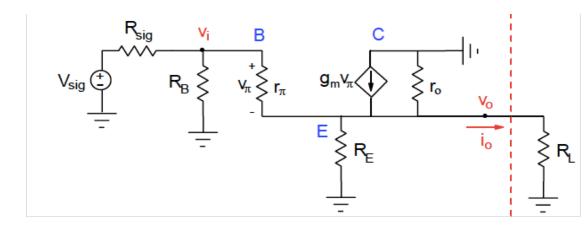
$$A_{vo} = \frac{g_m(R_S || r_o)}{1 + g_m(R_S || r_o)}$$

$$R_o = (1/g_m) \mid\mid R_S \mid\mid r_o$$

$$R_i = R_G$$



common collector BJT amplifier:



Some notes on source follower and emitter follower amplifiers:

- They have a voltage gain of lower than but close to unity.
- They have a low output resistance and a high input resistance.
- They are usually used as a voltage buffer.

source follower

$$A_{vo} = \frac{g_m(R_S || r_o)}{1 + g_m(R_S || r_o)}$$

$$R_o = (1/g_m) || R_S || r_o$$

$$R_i = R_G$$

emitter follower

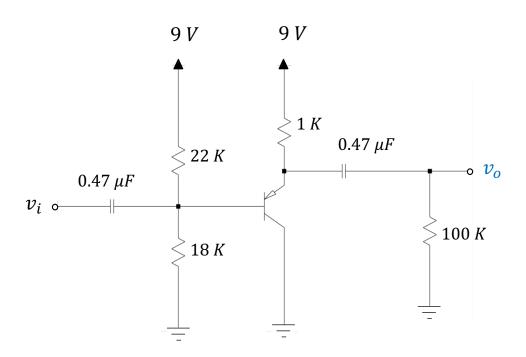
$$A_{vo} = \frac{g_m(R_E || r_o)}{1 + g_m(R_E || r_o)}$$

$$R_o = (1/g_m) || r_{\pi} || R_E || r_o$$

$$R_i = R_B || [r_{\pi} + (\beta + 1)(r_o || R_E || R_L)]$$

In the following circuit, find the amplifier parameters, R_o , R_i , A_{vo} .

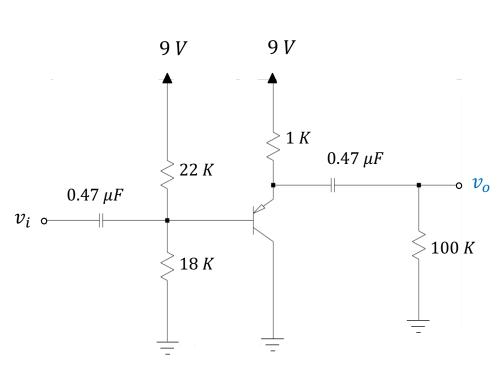
Let $\beta=100,\ V_T=25\ mV,\ V_A=150\ V.$ Ignore the early effect in bias calculations.



$$I_{E} = I_{C} + I_{B} = I_{C} + \frac{I_{C}}{S} = \frac{|S_{P}|}{|S|} I_{C}$$

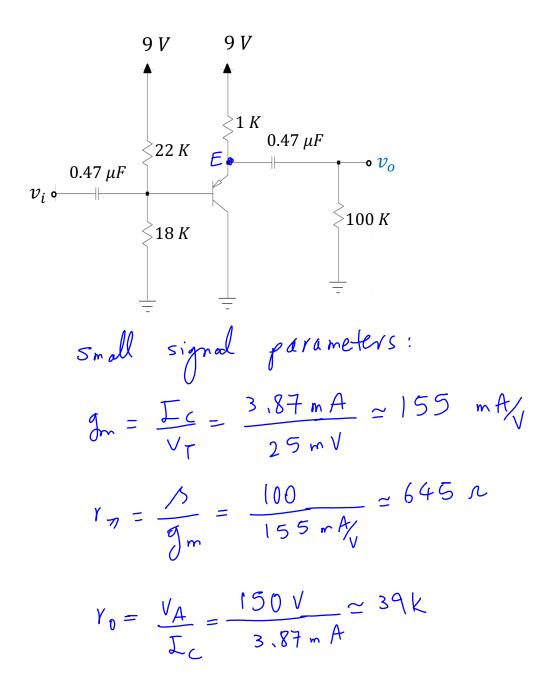
In the following circuit, find the amplifier parameters, R_o , R_i , A_{vo} .

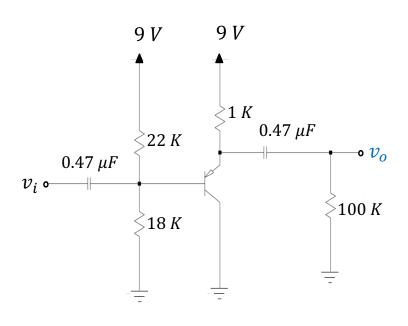
Let $\beta=100,\ V_T=25\ mV,\ V_A=150\ V.$ Ignore the early effect in bias calculations.



$$I_{E} = 3.87 \text{ mA}$$
 $I_{S} = 38.3 \text{ MA}$
 $I_{C} = I_{E} = 3.87 \text{ mA}$
 $V_{EC} = 9V - 1k \times I_{E}$

$$V_{BB} = \frac{18 \text{ ks}}{18 \text{ ks} + 22 \text{ ks}} \times 9V = 4.05 \text{ V}$$





Amplifier parameters:

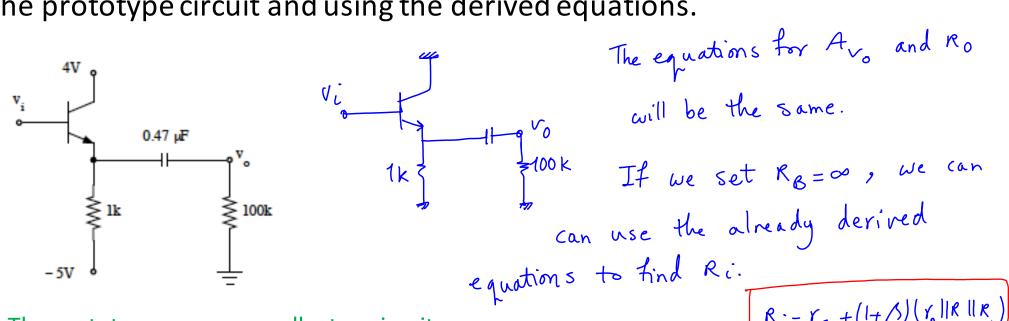
$$A_{V_0} = \frac{g_m(R_E || I_0)}{1 + g_m(R_E || I_0)} = \frac{155 \, \text{mAy}(39 \, \text{k} || 1 \, \text{k})}{1 + 155 \, \text{mAy}(39 \, \text{k} || 1 \, \text{k})}$$

$$R_i = R_B \| [r_n + 101 \times (r_0 \| R_E \| R_L)] \simeq 9 \text{ kg}$$

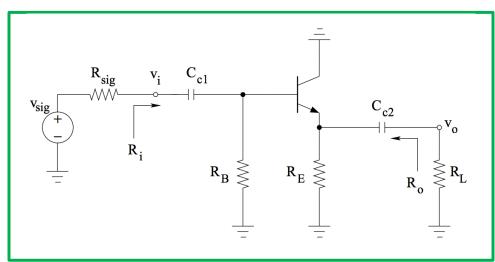
$$R_0 = (\frac{1}{g_m}) \| r_n \| R_E \| r_0 \simeq 6.3 \text{ g}$$

Discussion question 1 \wedge , \vee , \vee , \vee , \vee , will be given to you.

Write the A_{vo} , R_o , R_i equations for the following circuit by comparing it to the prototype circuit and using the derived equations.



The prototype common-collector circuit:



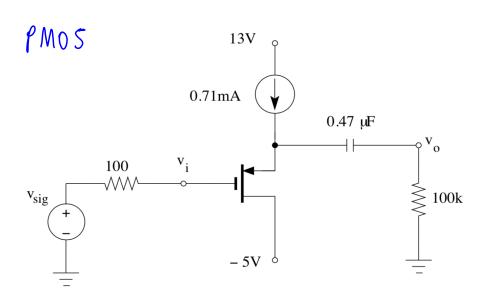
$$A_{vo} = \frac{g_m(R_E || r_o)}{1 + g_m(R_E || r_o)} \frac{R_i = r_p + (1 + f)(r_o || R_i || r_o)}{r_o || R_i || r_o || R_i ||$$

$$R_o = (1/g_m) || r_\pi || R_E || r_o$$

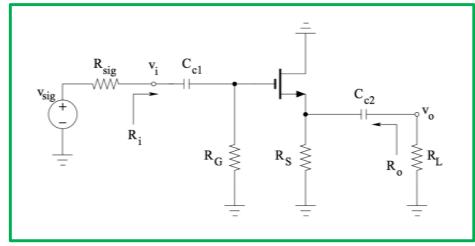
$$R_i = R_B || [r_{\pi} + (\beta + 1)(r_o || R_E || R_L)]$$

Discussion question 2

Write the A_{vo} , R_o , R_i equations for the following circuit by comparing it to the prototype circuit and using the derived equations.



The prototype common-drain circuit:



Comparing the given circuit with the prototype circuit, we can use the already derived equations by $\text{Setting } R_G = \infty \text{ and } R_S = \infty$ $\text{Avo} = \frac{9m^{70}}{1+9m^{70}}, R_0 = (\frac{1}{9m}) \parallel r_0, R_i = \infty$

$$A_{vo} = \frac{g_m(R_S || r_o)}{1 + g_m(R_S || r_o)}$$

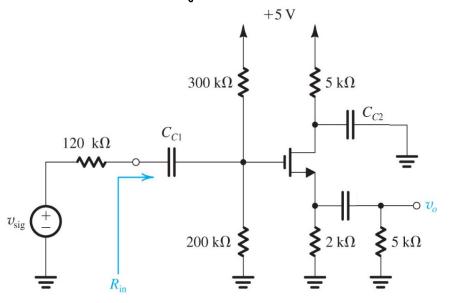
$$R_o = (1/g_m) || R_S || r_o$$

$$R_i = R_G$$

Discussion question 3.

The NMOS in the below amplifier has $V_{tn}=0.7~V$ and $V_A=50~\rm V$. Neglecting the early effect, verify that the transistor is in saturation with $I_D=0.5~\rm mA$ and $V_{OV}=0.3~\rm V$. What must the MOSFET's k_n be? What is the DC voltage at the drain?

Find R_i and A_{v_i} .



 $k_n = \frac{2 \pm D}{V^2} \Rightarrow k_n = 11.1 \text{ m A}/2$

Bias circuit:

$$5v$$
 $5v$
 5

$$V_G = \frac{200 \, \text{kg}}{200 \, \text{k} + 300 \, \text{k}} \times 5V = 2V$$

$$I_{D} = 0.5 \longrightarrow V_{S} = 2k \times I_{D} = 1V \longrightarrow V_{S} = 1V$$

$$V_{D} = 5V - 5k \times I_{D} = 2.5V \longrightarrow V_{D} = 2.5V$$

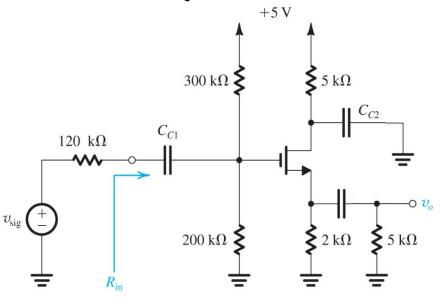
Transistor is in Saturation

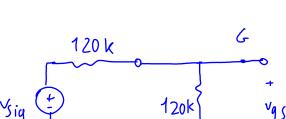
Discussion question 3.

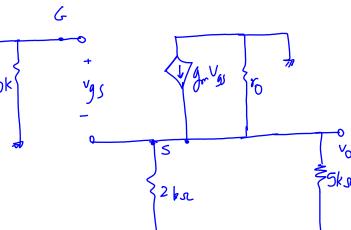
The NMOS in the below amplifier has $V_{tn}=0.7\ V$ and $V_A=50\ V$. Neglecting the early effect, verify that the transistor is in saturation with $I_D=0.5~\mathrm{mA}$ and $V_{OV}=0.3~\mathrm{V}$. What $g_{m} = \frac{2I_{D}}{V_{OV}} = 3.3 \text{ m/s}$ $Y_{0} = \frac{1}{\lambda \cdot I_{D}} = \frac{V_{A}}{I_{D}} = 100 \text{kg}$

must the MOSFET's k_n be? What is the DC voltage at the drain?

Find R_i and A_{v_i} .







$$A_{V_0} = \frac{g_m(R_S || r_0)}{1 + g_m(R_S || r_0)} = \frac{3.3 m / (2 k || 100 k)}{1 + 3.3 m / (2 k || 100 k)}$$